

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

BSX45, -10, -16
BSX46, -10, -16
BSX47, -10,

NPN SILICON TRANSISTORS

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR BSX45 series types are NPN Silicon Epitaxial Transistors designed for general purpose amplifier and switching applications.

MAXIMUM RATINGS ($T_A=25^\circ\text{C}$)

	SYMBOL	BSX45	BSX46	BSX47	UNITS
Collector-Base Voltage	V_{CBO}	80	100	120	V
Collector-Emitter Voltage	V_{CEO}	40	60	80	V
Emitter-Base Voltage	V_{EBO}		7.0		V
Collector Current	I_C		1.0		A
Collector Current (Peak)	I_{CM}		1.5		A
Base Current (Peak)	I_{BM}		200		mA
Power Dissipation ($T_C=25^\circ\text{C}$)	P_D		6.25		W
Power Dissipation	P_D		0.8		W
Operating and Storage					
Junction Temperature	T_J, T_{stg}		-65 to +200		$^\circ\text{C}$
Thermal Resistance	Θ_{JC}		28		$^\circ\text{C/W}$
Thermal Resistance	Θ_{JA}		219		$^\circ\text{C/W}$

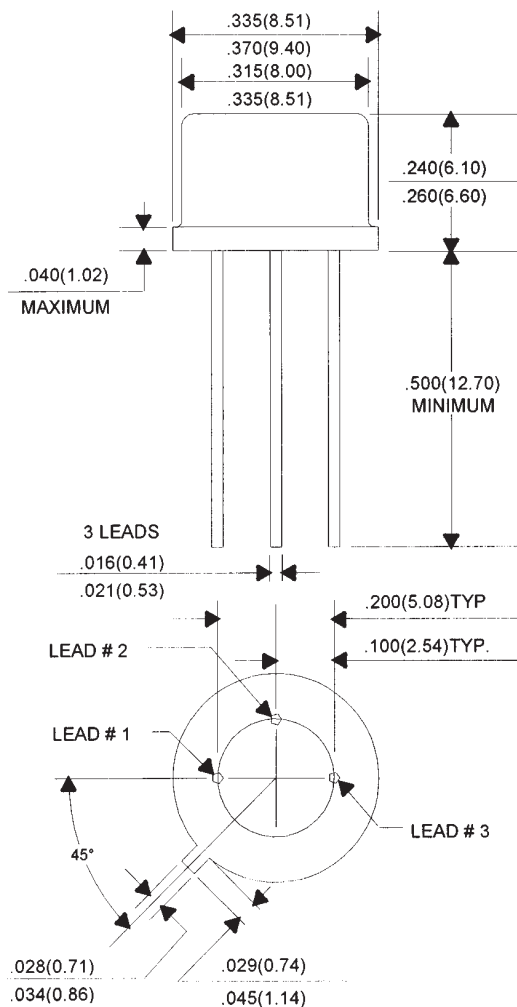
ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	BSX45		BSX46		BSX47		UNITS
		MIN	MAX	MIN	MAX	MIN	MAX	
I_{CBO}	$V_{CB}=60\text{V}$		30		30		-	nA
I_{CBO}	$V_{CB}=60\text{V}, T_A=150^\circ\text{C}$		10		10		-	μA
I_{CBO}	$V_{CB}=80\text{V}$		-		-		30	nA
I_{CBO}	$V_{CB}=80\text{V}, T_A=150^\circ\text{C}$		-		-		10	μA
I_{EBO}	$V_{EB}=5.0\text{V}$		10		10		10	nA
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		1.0		1.0		-	V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=25\text{mA}$		-		-		0.9	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=100\text{mA}$		1.0		1.0		1.0	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=500\text{mA}$	0.75	1.5	0.75	1.5	0.75	1.5	V
$V_{BE(ON)}$	$V_{CE}=1.0\text{V}, I_C=1.0\text{A}$		2.0		2.0		2.0	V
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	50		50		50		MHz
C_c	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		25		20		15	pF
C_e	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		80		80		80	pF
t_{on}	$I_C=100\text{mA}, I_{B1}=I_{B2}=5.0\text{mA}$		200		200		200	ns
t_{off}	$I_C=100\text{mA}, I_{B1}=I_{B2}=5.0\text{mA}$		850		850		850	ns
NF	$V_{CE}=5.0\text{V}, I_C=100\mu\text{A}, R_S=1.0\text{k}\Omega,$ $f=1.0\text{kHz}, BW=200\text{Hz}$		3.5 TYP		3.5 TYP		3.5 TYP	dB

(Continued on Reverse Side)

SYMBOL	TEST CONDITIONS	BSX45-10 BSX46-10 BSX47-10			BSX45-16 BSX46-16			UNITS
		MIN	TYP	MAX	MIN	TYP	MAX	
h_{FE}	$V_{CE}=1.0V, I_C=100\mu A$	15			25			
h_{FE}	$V_{CE}=1.0V, I_C=100mA$	63		160	100		250	
h_{FE}	$V_{CE}=1.0V, I_C=500mA$	25			35			
h_{FE}	$V_{CE}=1.0V, I_C=1.0A$		20			30		

JEDEC TO-39 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).

Lead Code:

1. Emitter
2. Base
3. Collector

Central™

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824